



GaN-based UV photodiode

Model: GT-ABC-XL

General Features:

- Broad band UVA+UVB+UVC photodiode
- Photovoltaic mode operation
- TO-39 metal housing
- Good visible blindness
- High responsivity and low dark current

Applications: UV index monitoring, UV radiation dose measurement, flame detection

Specifications:

Parameters	Symbol	Value	Unit	
Maximum ratings				
Operation temperature range	T_{opt}	-25-85	°C	
Storage temperature range	T_{sto}	-40-85	°C	
Soldering temperature (3 s)	T_{sol}	260	°C	
Reverse voltage	V_{r-max}	-10	V	
General characteristics (25 °C)				
Chip size	A	4	mm ²	
Dark current ($V_r = -1$ V)	I_d	61	nA	A
Temperature coefficient	T_c	0.05	%/ °C	
Capacitance (at 0 V and 1 MHz)				

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where A is chip area, P is incident UV power density and R_{λ} is responsivity at specific wavelength.

Manufactured by GaNo Optoelectronics Inc. Suzhou, China